A Three-Transistor-Cell, 1024-Bit, 500NS MOS RAM

The 1970 paper by Regitz (Honeywell) and Karp (Intel) was the groundbreaking work for the future development of DRAMs. Using a three-transistor cell, 1024 bit memory density was achieved. The read speed for this device was 345ns and the power consumption was 50\(\mu W\) per bit. The “16 pin package” used in this work became the DRAM package of choice for many years to come.